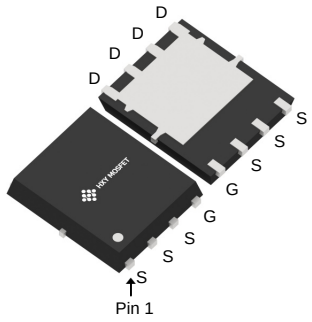
SM6442D1RL

N-Channel Enhancement Mode MOSFET

Description

The SM6442D1RL uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



DFN5X6-8L
(TDFN-8(5.2x5.9))

General Features

V_{DS} = 40V I_D = 70A

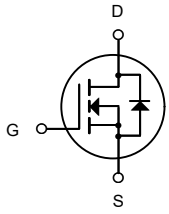
$R_{DS(ON)}$ < 8.5mΩ @ V_{GS}=10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
SM6442D1RL	DFN5X6-8L(TDFN-8(5.2x5.9))	HXY MOSFET	5000

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ 10V[1]	70	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ 10V[1]	44	A
I_{DM}	Pulsed Drain Current[2]	280	A
EAS	Single Pulse Avalanche Energy[3]	76	mJ
P_D@T_C=25°C	Total Power Dissipation[4]	72.3	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient (Steady State)[1]	62	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case[1]	1.73	°C/W

Electrical Characteristics (Ta=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	40	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=10A	---	7.5	8.5	mΩ
		V_{GS}=4.5V , I_D=5A	---	10	15	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.0	1.7	3	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=32V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=32V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=10V , I_D=5A	---	13	---	S
Q_g	Total Gate Charge (4.5V)	V_{DS}=20V , V_{GS}=10V , I_D=10A	---	20	---	nC
Q_{gs}	Gate-Source Charge		---	2.8	---	
Q_{gd}	Gate-Drain Charge		---	5.1	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=15V , V_{GS}=10V R_G=3.3Ω I_D=1A	---	13.2	---	ns
T_r	Rise Time		---	2.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	72	---	
T_f	Fall Time		---	4.5	---	
C_{iss}	Input Capacitance	V_{DS}=25V , V_{GS}=0V , f=1MHz	---	1278	---	pF
C_{oss}	Output Capacitance		---	135	---	
C_{rss}	Reverse Transfer Capacitance		---	87	---	
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	70	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1	V

Note :

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.

3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=47A.

4.The power dissipation is limited by 150℃ junction temperature.

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

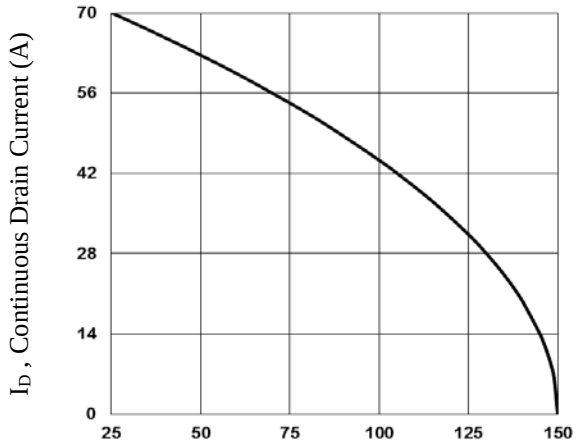


Fig.1 Continuous Drain Current vs. T_C

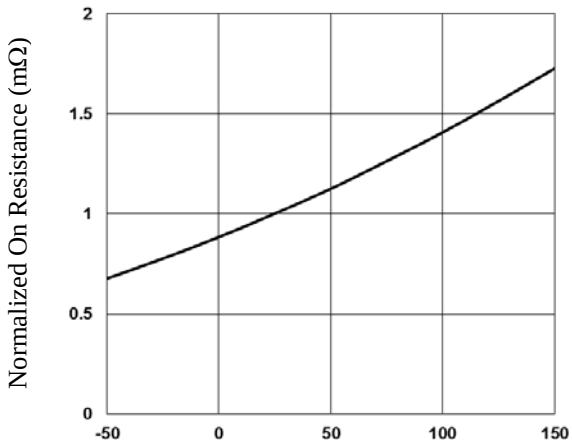


Fig.2 Normalized RDSON vs. T_J

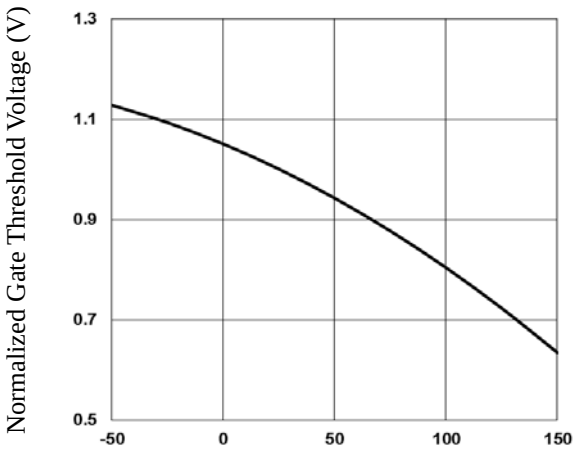


Fig.3 Normalized V_{th} vs. T_J

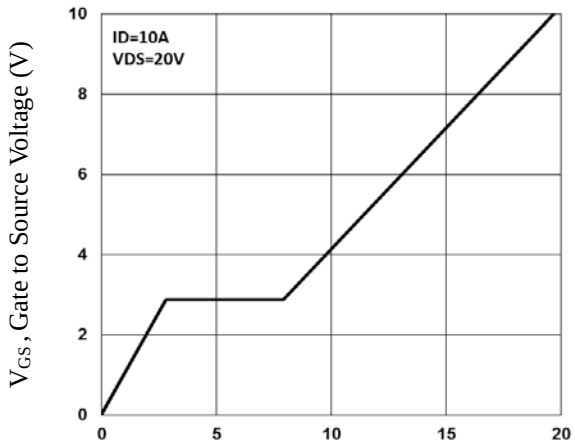


Fig.4 Gate Charge Waveform

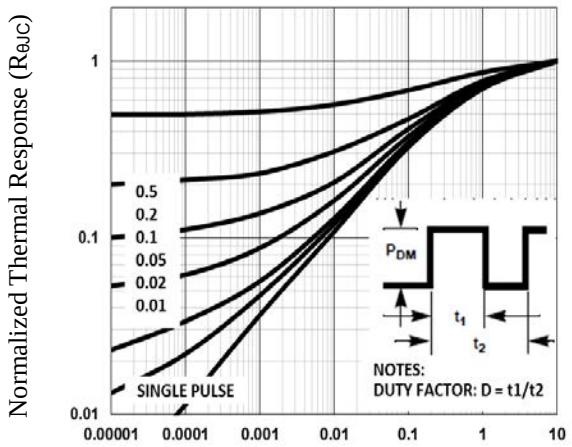


Fig.5 Normalized Transient Impedance

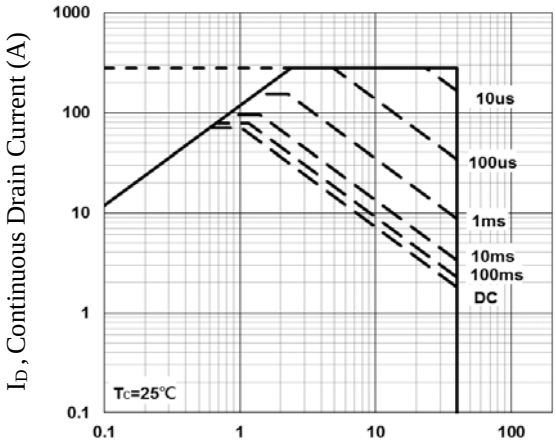


Fig.6 Maximum Safe Operation Area

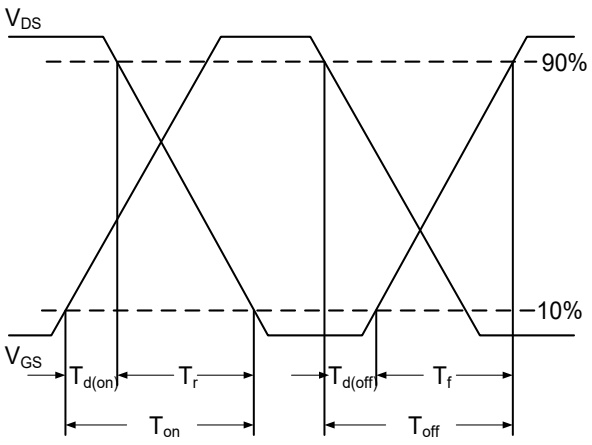


Fig.7 Switching Time Waveform

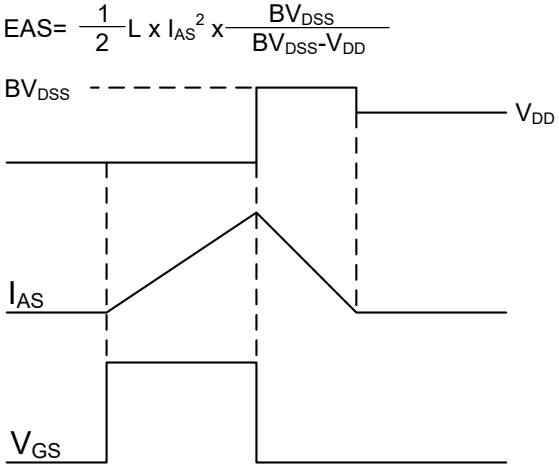
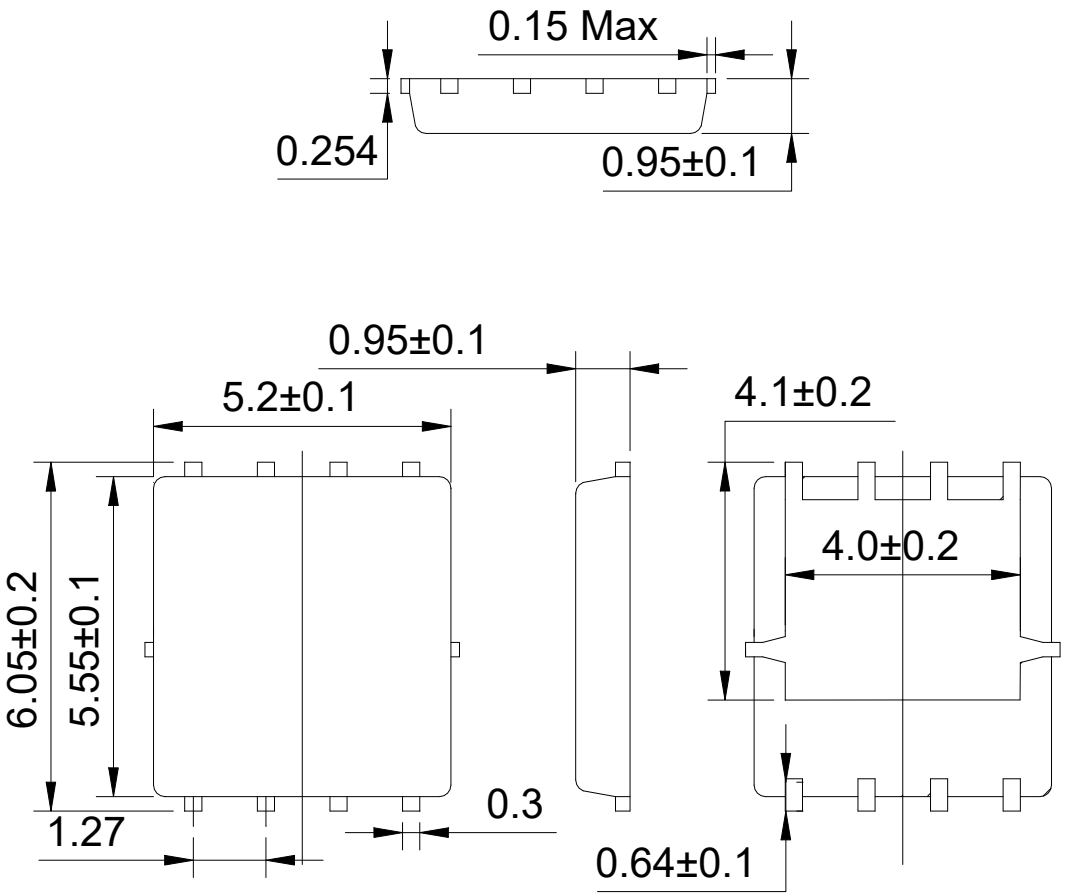


Fig.8 EAS Waveform

DFN5X6-8L Package Information

Unit:mm



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